

## ATTACHMENT A Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) An etching solution ~~comprising~~ consisting essentially of:
  - (i) hydrofluoric acid;
  - (ii) water in a concentration of 30% by weight or lower; and
  - (iii) at least one member selected from the group consisting of an organic acid, an inorganic acid having a pKa at 25°C of about 2 and an organic solvent having a hetero atom, whose content ranges from 70 to 99.9% by weight,wherein the etching solution has a ratio of an etch rate of a boron silicate glass film (BSG) or boron phosphosilicate glass / an etch rate of a thermal oxide film (THOX) at 25°C of 20 or higher.
2. (Previously Presented) The etching solution according to claim 1, wherein the organic solvent has a relative dielectric constant of 61 or lower.
3. (Cancelled)
4. (Cancelled)

5. (Previously Presented) The etching solution according to claim 1, wherein the organic solvent is isopropyl alcohol.

6. (Previously Presented) The etching solution according to claim 1, wherein the organic acid is acetic acid.

7. (Previously Presented) The etching solution according to claim 1, wherein the organic solvent comprises tetrahydrofuran.

8. (Previously Presented) The etching solution according to claim 1, wherein the organic solvent is acetone.

9. (Previously Presented) The etching solution according to claim 1, wherein the organic solvent comprises methanol.

10. (Previously Presented) The etching solution according to claim 1, wherein the organic solvent comprises ethanol.

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Previously Presented) A method for producing an etched article by etching an article to be etched with the etching solution as defined in claim 1.

16. (Original) An etched article which is obtainable by the method of claim 15.